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Thermal and ion-beam-induced etching of InP with chlorine

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Abstract. Surface spectroscopic techniques have been used to investigate adsorption and thermal and ion-induced processes at the InP(100)–Cl₂ interface. Two adsorption states are identified and etching reactions are interpreted in terms of surface chemical transformations and desorption processes involving these states.

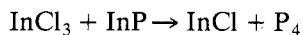
1. Adsorption and thermal desorption

Chlorine was exposed at 300 K to a (4 × 2) reconstructed InP(100) surface and Auger and thermal desorption spectroscopies used to investigate the adsorption. The uptake characteristics from the Auger data were of the type observed for many halogen chemisorption systems [1], showing initial rapid uptake, attributed to adsorption into a halogen overlayer, followed by much slower uptake into a multilayer corrosion phase. Analysis of the P : In Auger signal ratio as a function of Cl coverage indicated P depletion in the corrosion phase.

Thermal desorption spectra for varying chlorine exposures and desorbing masses are illustrated in figure 1. Two states are observed: a strongly bound state (labelled β), with uptake characteristics that correspond to the submonolayer state, and a weakly bound state (labelled α), corresponding to the corrosion phase. Cracking pattern analysis indicated that the α -state desorbs as InCl₃, while the β -state products are P₄ and InCl.

2. The ion-beam-induced process

In order to increase the rate of etching at low temperatures ion beam irradiation of the adsorbed phases was investigated. Following a 500 L chlorine exposure the surface was irradiated for various intervals with a 500 eV Ar⁺-ion beam and the surface analysed by TDS. The results showed initially the rapid loss of the α -state InCl₃ desorption peak but with *negligible* change in chlorine coverage. Simultaneously the InCl and P₄ desorption peaks increased in size. The initial effect of the ion beam therefore appears to be to induce the transformation



Subsequent irradiation results in the desorption of these products. Etching therefore

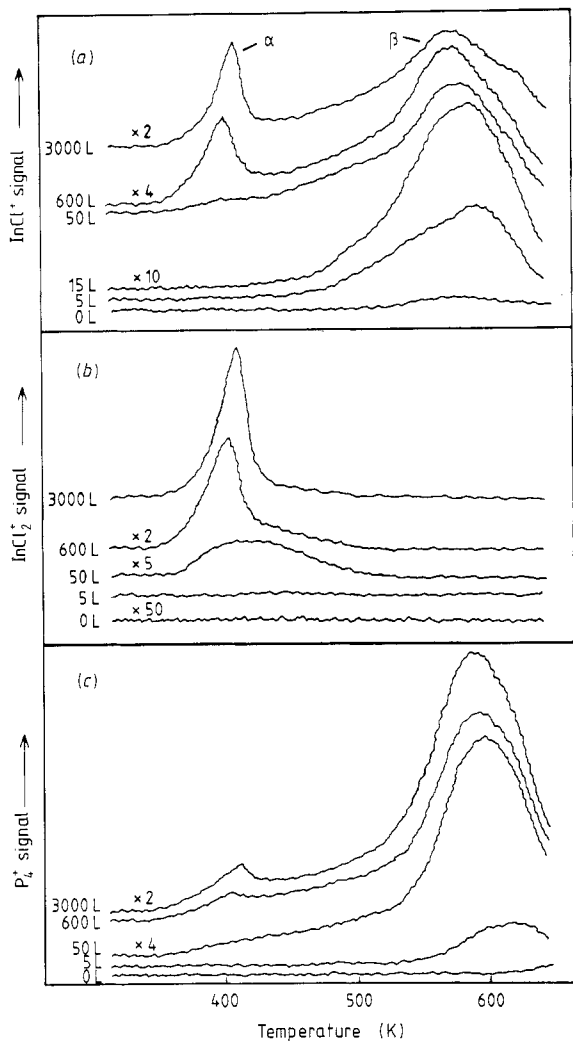


Figure 1. Thermal desorption spectra for (a) InCl, (b) InCl₂ and (c) P₄ plotted as a fraction of Cl₂ exposure (given by curves).

appears in this case to be a two-ion process. This is inconsistent with the thermal pulse model proposed in [2] and may be better described by a two-step collisional cascade mechanism [3].

References

- [1] Jackman R B, Ebert H and Foord J S 1986 *Surf. Sci.* **176** 183
- [2] McNevin S C 1986 *J. Vac. Sci. Technol. B* **4** 1203
- [3] Dieleman J, Sanders F H M, Kolfshoten A W, Zalm P C, de Vries A E and Haring A 1985 *J. Vac. Sci. Technol. B* **3** 1384